





**INA132** SBOS059A - NOVEMBER 1996 - REVISED FEBRUARY 2024

# **INA132 Low Power, Single-Supply Difference Amplifier**

#### 1 Features

Wide supply range:

 Single supply: 2.7V to 36V - Dual supplies: ±1.35V to ±18V

DC precision performance:

Low gain error: ±0.075% (maximum)

Low nonlinearity: 0.001% (maximum)

High common-mode rejection: 90dB (typical)

Low quiescent current: 175µA

# 2 Applications

Optical modules

**Building security gateways** 

AC analog input module

Mass spectrometer

CPU (PLC Controller)

Lab and field instrumentation

#### 3 Description

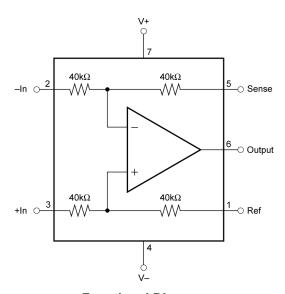
The INA132 is a low-power, unity-gain differential amplifier consisting of a precision op amp with a precision resistor network. The on-chip resistors are laser trimmed for accurate gain and high common-mode rejection. Excellent TCR tracking of the resistors maintains gain accuracy and commonmode rejection over temperature. The internal op amp common-mode range extends to the negative supply —an excellent choice for single-supply applications. The INA132 operates on single (2.7V to 36V) or dual (±1.35V to ±18V) supplies.

The differential amplifier is the foundation of many commonly used circuits. The INA132 provides this circuit function without using an expensive precision resistor network. The INA132 is available in an SO-8 surface-mount package and operates over the industrial temperature range of -40°C to +85°C.

#### **Package Information**

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>
INA132	D (SOIC, 8)	4.9mm × 6mm

- For more information, see Section 9.
- The package size (length × width) is a nominal value and includes pins, where applicable.



**Functional Diagram** 

# **Table of Contents**

1 Features	1	6 Application and Implementation	9
2 Applications		6.1 Applications Information	
3 Description	1	6.2 Typical Applications	.11
4 Pin Configuration and Functions	2	7 Device and Documentation Support	
5 Specifications	3	7.1 Receiving Notification of Documentation Updates	.14
5.1 Absolute Maximum Ratings		7.2 Support Resources	14
5.2 ESD Ratings	3		
5.3 Recommended Operating Conditions			.14
5.4 Thermal Information			.14
5.5 Electrical Characteristics: V <sub>S</sub> = ±15V	4	8 Revision History	14
5.6 Electrical Characteristics: V <sub>S</sub> = 5V	5		
5.7 Typical Characteristics	6		

# **4 Pin Configuration and Functions**

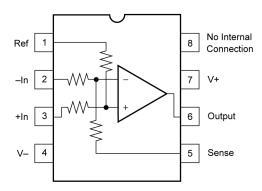


Figure 4-1. D Package, 8-Pin SOIC (Top View)

## **Table 4-1. Pin Functions**

PIN		TYPE	DESCRIPTION		
NAME	NO.	ITPE	DESCRIPTION		
-In	2	Input	Negative (inverting) input		
+In	3	Input	Positive (noninverting) input		
No Internal Connection	8	_	No internal connection. Leave unconnected.		
Output	6	Output	Output		
Ref	1	_	Reference input. Drive this pin with a low impedance source. Interchanging pin 1 and 3 degrade CMR.		
Sense	5	_	Sense input. Drive this pin with a low impedance source. Interchanging pin 2 and 5 degrade CMR.		
V-	4	Input	Negative supply		
V+	7	Input	Positive supply		



# **5 Specifications**

## 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
Vs	Cupply voltage	Dual supply, $V_S = (V+) - (V-)$		±18	V
V <sub>S</sub>	Supply voltage	Single supply, $V_S = (V+) - 0V$		36	V
	Input voltage range	·		±80	V
	Output short-circuit to (V <sub>S</sub> / 2)		Continuous		
T <sub>A</sub>	Operating temperature		<b>–</b> 55	125	°C
TJ	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-55		°C
	Lead temperature (soldering, 10s)			300	°C

<sup>(1)</sup> Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

# 5.2 ESD Ratings

				VALUE	UNIT
V		Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±750	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	±1000	V	

- 1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

## **5.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)

				MAX	UNIT
V <sub>S</sub>	Supply voltage	Single-supply	2.7	36	V
		Dual-supply	±1.35	±18	V
T <sub>A</sub>	Specified temperature		-40	85	°C

#### 5.4 Thermal Information

		INA132	
	THERMAL METRIC(1)		UNIT
		8 PINS	
θ <sub>JA</sub> Junction-to-ambient thermal resistance		150	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



5.5 Electrical Characteristics:  $V_S$  = ±15 $V_S$  at  $T_A$  = 25°C,  $V_S$  = ±15 $V_S$ ,  $V_S$  = 10 $V_S$ ,  $V_S$  = 0,  $V_S$ , and  $V_S$  = 10 (unless otherwise noted)

	PARAMETER	TEST CONDITION	ONS	MIN	TYP	MAX	UNIT
INPUT				<u> </u>			
.,	0,5 (1)	570	INA132		±75	±250	.,
Vos	Offset voltage <sup>(1)</sup>	RTO	INA132A		±75	±500	μV
	0% + 1 + 1 : (1)	DTO T 40004 10500	INA132		±1	±5	11/1°C
	Offset voltage drift <sup>(1)</sup>	RTO, $T_A = -40^{\circ}C$ to +85°C	INA132A		±1	±10 <sup>(4)</sup>	μV/°C
	Long-term stability <sup>(1)</sup>				±0.3		μV/mo
PSRR	Power-supply rejection ratio <sup>(1)</sup>	RTO, $V_S = \pm 1.35V$ to $\pm 18V$			±5	±30	μV/V
V <sub>CM</sub>	Common-mode voltage	V <sub>O</sub> = 0V		(V-)		2(V+) - 2	V
CMRR	Common-mode rejection	$V_{CM} = -15V \text{ to } +28V, R_S = 0\Omega$	INA132	76	90		dB
CIVIKK	Common-mode rejection	V <sub>CM</sub> = -13V to +26V, K <sub>S</sub> = 012	INA132A	70	90		dB
	Differential input impedance <sup>(2)</sup>		·		80		kΩ
	Common-mode input impedance <sup>(2)</sup>				80		kΩ
NOISE		•				,	
_	RTO, f <sub>B</sub> = 0.1Hz to 10Hz				1.6		$\mu V_{PP}$
e <sub>N</sub>	Voltage noise <sup>(3)</sup>	RTO, f = 1kHz			75		nV/√ <del>Hz</del>
GAIN		•				,	
	Gain				1		V/V
CE	Gain error	V <sub>O</sub> = -14V to +13.5V	INA132		±0.01	±0.075	%
GE			INA132A		±0.01	±0.1	70
	Gain error drift <sup>(4)</sup>	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	$T_A = -40$ °C to +85°C		±1	±10	ppm/°C
	Coin poplinocrity	$V_{O} = -14V \text{ to } +13.5V$	INA132		±0.0001	±0.001	% of FSR
	Gain nonlinearity	V <sub>0</sub> = -14V to +13.5V	INA132A		±0.0001	±0.002	% 01 FSR
OUTPL	JT						
	Positive output voltage swing	R <sub>L</sub> = 100kΩ		(V+) – 1	(V+) - 0.8		V
	Positive output voltage swing	$R_L = 10k\Omega$		(V+) – 1.5	(V+) - 0.8		V
	Negative output voltage swing	R <sub>L</sub> = 100kΩ		(V-) + 0.5	(V-) + 0.15		٧
	Negative output voltage swilig	$R_L = 10k\Omega$		(V-) + 1	(V-) + 0.25		V
$C_L$	Load capacitance	Stable operation			10000		pF
I <sub>SC</sub>	Short-circuit current	Continuous to V <sub>S</sub> / 2			+6/–15		mA
FREQU	JENCY RESPONSE						
BW	Small signal bandwidth, –3dB				300		kHz
SR	Slew rate				0.1		V/µs
+	Sattling time	V = 10V stop	0.1%		85		116
t <sub>S</sub>	Settling time	V <sub>O</sub> = 10V step 0.01%			88		μs
	Overload recovery time	50% input overdrive			7		μs
POWE	R SUPPLY					•	
IQ	Quiescent current	V <sub>IN</sub> = 0V			±175	±230	μA

- (1) Includes effects of amplifier input bias and offset currents.
- (2)  $40k\Omega$  resistors are ratio matched but have  $\pm 20\%$  absolute value.
- Includes effects of amplifier input current noise and thermal noise contribution of resistor network. (3)
- Specified by wafer test to 95% confidence level.



**5.6 Electrical Characteristics:**  $V_S = 5V$  at  $T_A = 25^{\circ}C$ ,  $V_S = +5V$ ,  $R_L = 10k\Omega$  connected to  $V_S/2$ ,  $V_{REF} = V_S/2$ ,  $V_{CM} = V_S/2$ , and G = 1 (unless otherwise noted)

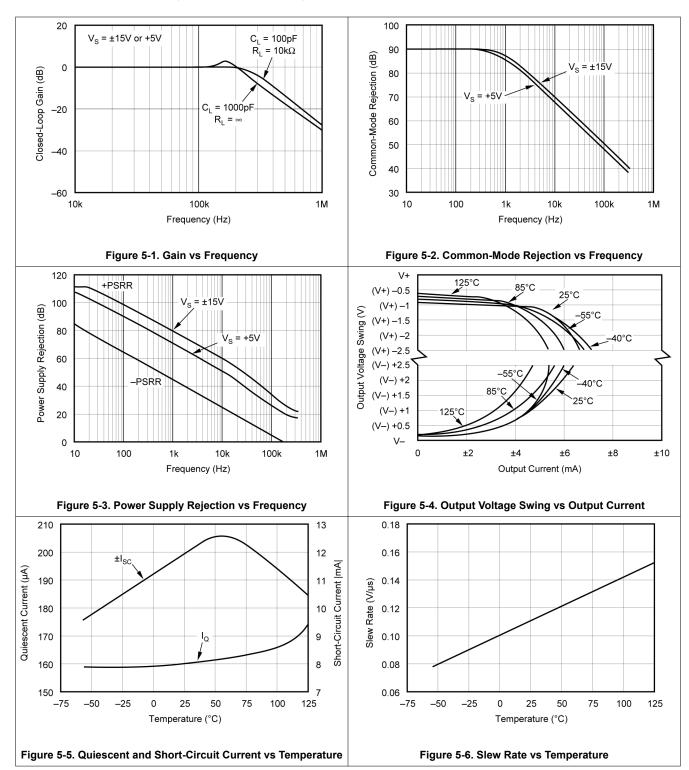
	PARAMETER	TEST CON	DITIONS	MIN	TYP	MAX	UNIT	
INPUT				<u>'</u>				
.,	Offset voltage <sup>(1)</sup>	DTO	INA132		±150	±500	/	
Vos		RTO	INA132A		±150	±750	μV	
	Offset voltage drift <sup>(1)</sup>	RTO, $T_A = -40^{\circ}\text{C}$ to +85°C			±2		μV/°C	
V <sub>CM</sub>	Common-mode voltage	V <sub>O</sub> = 0V	O = 0V			2(V+) - 2	V	
CMDD	Common-mode rejection	$V_{CM}$ = 0V to 8V, $R_S$ = 0 $\Omega$	INA132	76	90		dB	
CMRR			INA132A	70	90			
OUTPU	Т							
	Desitive systems veltage swing	R <sub>L</sub> = 100kΩ		(V+) – 1	(V+) - 0.75		V	
	Positive output voltage swing	R <sub>L</sub> = 10kΩ		(V+) – 1	(V+) - 0.8		V	
	Negative output voltage	R <sub>L</sub> = 100kΩ		(V-) + 0.25	(V-) + 0.06		V	
	swing	$R_L = 10k\Omega$		(V-) + 0.25	(V-) + 0.12		V	
POWER	RSUPPLY							
IQ	Quiescent current	V <sub>IN</sub> = 0V			±175	±230	μA	

<sup>(1)</sup> Includes effects of amplifier input bias and offset currents.



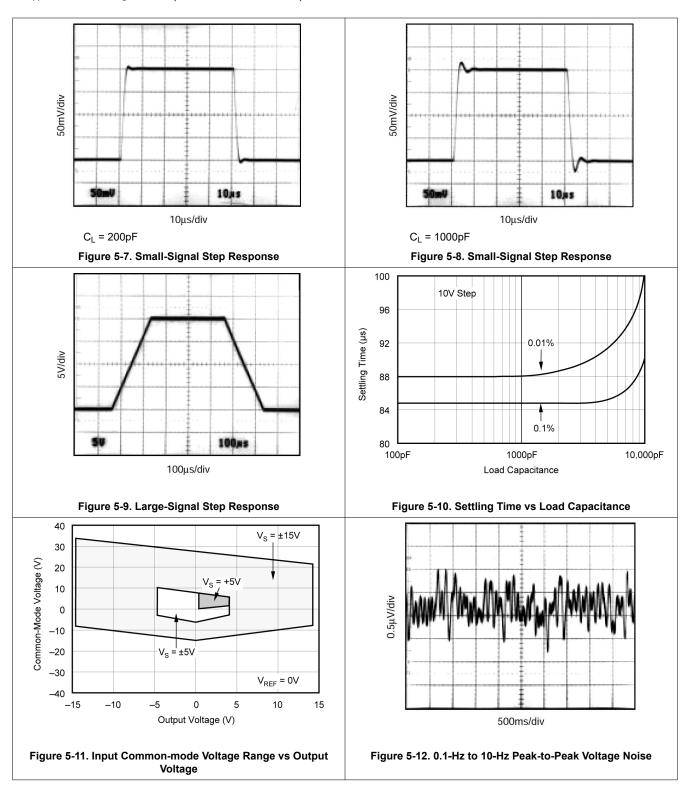
#### **5.7 Typical Characteristics**

at  $T_A = +25$ °C and  $V_S = \pm 15V$  (unless otherwise noted)



# **5.7 Typical Characteristics (continued)**

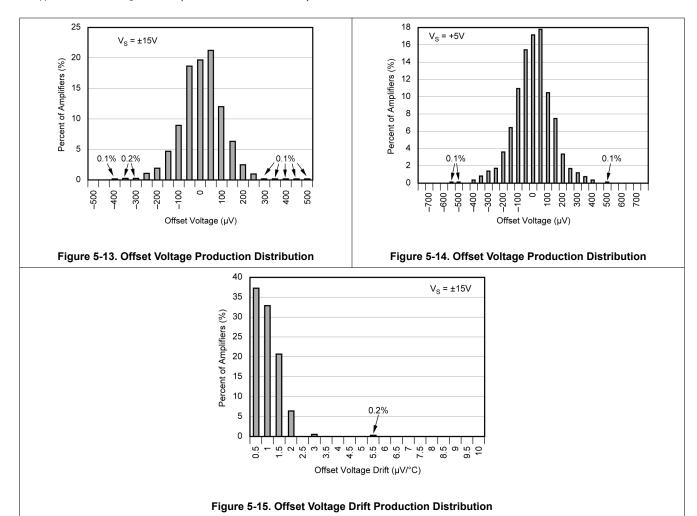
at  $T_A = +25$ °C and  $V_S = \pm 15V$  (unless otherwise noted)





## **5.7 Typical Characteristics (continued)**

at  $T_A = +25$ °C and  $V_S = \pm 15V$  (unless otherwise noted)





## **6 Application and Implementation**

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

#### **6.1 Applications Information**

Figure 6-1 shows the basic connections required for operation of the INA132. Connect power-supply bypass capacitors close to the device pins.

The differential input signal is connected to pins 2 and 3 as shown. Ensure that the source impedances connected to the inputs are nearly equal to maintain good common-mode rejection. An  $8\Omega$  mismatch in source impedance degrades the common-mode rejection of a typical device to approximately 80dB. Gain accuracy is also slightly affected. If the source has a known impedance mismatch, use an additional resistor in series with one input to preserve good common-mode rejection.

Do not interchange pins 1 and 3 or pins 2 and 5, even though nominal resistor values are equal. These resistors are laser trimmed for precise resistor ratios to achieve accurate gain and highest CMR. Interchanging these pins does not provide specified performance. Sense measurements at the load, as in Figure 6-1.

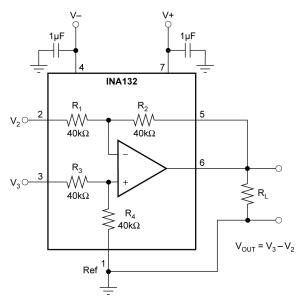


Figure 6-1. Basic Power Supply and Signal Connections

#### 6.1.1 Operating Voltage

The INA132 operates from single (2.7V to 36V) or dual  $(\pm 1.35V$  to  $\pm 18V)$  supplies with excellent performance. Specifications are production tested with +5V and  $\pm 15V$  supplies. Most behavior remains unchanged throughout the full operating voltage range. Parameters that vary significantly with operating voltage are shown in the *Typical Characteristics*.

The internal op amp in the INA132 is a single-supply design. This design allows linear operation with the op-amp common-mode voltage equal to, or slightly below V– (or single supply ground). Although input voltages on pins 2 and 3 that are less than the negative supply voltage do not damage the device, operation in this region is not recommended. Transient conditions at the inverting input terminal less than the negative supply can cause a positive feedback condition that can lock the INA132 output to the negative rail.

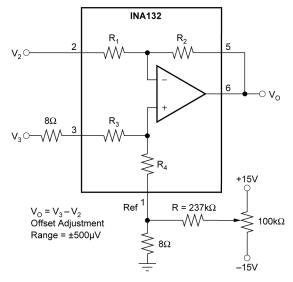
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The INA132 can accurately measure differential signals that are greater than the positive power supply. The linear common-mode range extends to nearly twice the positive power supply voltage—see typical characteristics curve, *Common-Mode Range vs Output Voltage*.

# 6.1.2 Offset Voltage Trim

The INA132 is laser trimmed for low offset voltage and drift. Most applications require no external offset adjustment. Figure 6-2 shows an optional circuit for trimming the output offset voltage. The output is referred to the output reference terminal (pin 1), which is normally grounded. A voltage applied to the Ref terminal is summed with the output signal, and can be used to null offset voltage. Ensure that the source impedance of a signal applied to the Ref terminal is less than  $8\Omega$  to maintain good common-mode rejection. To maintain low impedance at the Ref terminal, the trim voltage can be buffered with an op amp, such as the OPA177.



NOTE: For  $\pm 750 \mu V$  range, R =  $158 k\Omega$ .

Figure 6-2. Offset Adjustment.

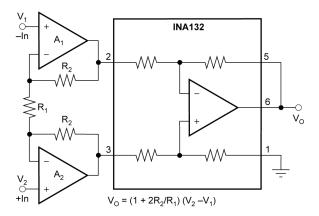
#### 6.1.3 Capacitive Load Drive Capability

The INA132 drives large capacitive loads, even at low supplies. The device is stable with a 10,000-pF load. See the *Small-Signal Step Response* and *Settling Time vs Load Capacitance* typical characteristics.

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# **6.2 Typical Applications**



The INA132 can be combined with op amps to form a complete instrumentation amplifier with specialized performance characteristics. Burr-Brown offers many complete high performance IAs. Products with related performances are shown at the right.

A <sub>1</sub> , A <sub>2</sub>	FEATURE	SIMILIAR COMPLETE BURR-BROWN IA
OPA27	Low Noise	INA103
OPA129	Ultra Low Bias Current (fA)	INA116
OPA177	Low Offset Drift, Low Noise	INA114,INA128
OPA2130	Low Power, FET-Input (pA)	INA111
OPA2234	Single Supply, Precision,	
	Low Power	INA122 <sup>(1)</sup> , INA118
OPA2237	Single Supply, Low Power,	INIA 100(1) INIA 100(1)
	MSOP-8	INA122 <sup>(1)</sup> , INA126 <sup>(1)</sup>

NOTE: (1) Available 1Q'97.

Figure 6-3. Precision Instrumentation Amplifier

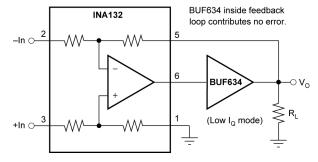


Figure 6-4. Low Power, High Output Current Precision Difference Amplifier



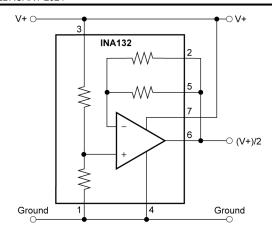


Figure 6-5. Pseudoground Generator

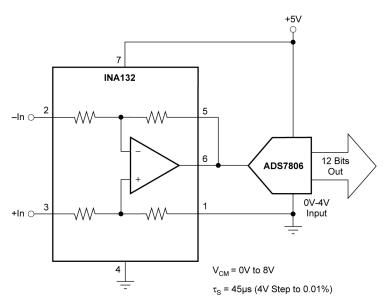


Figure 6-6. Differential Input Data Acquisition

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Set R<sub>1</sub> = R<sub>2</sub>

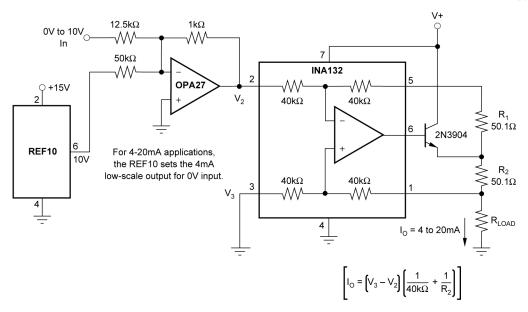


Figure 6-7. Precision Voltage-to-Current Conversion

The difference amplifier is a highly versatile building block that is useful in a wide variety of applications. See the INA105 data sheet for additional applications ideas, including:

- · Current receiver with compliance to rails
- · Precision unity-gain inverting amplifier
- ±10-V precision voltage reference
- ±5-V precision voltage reference
- · Precision unity-gain buffer
- · Precision average value amplifier
- Precision G = 2 amplifier
- · Precision summing amplifier
- Precision G = 1/2 amplifier
- · Precision bipolar offsetting
- · Precision summing amplifier with gain
- Instrumentation amplifier guard drive generator
- Precision summing instrumentation amplifier
- · Precision absolute value buffer
- Precision voltage-to-current converter with differential inputs
- Differential input voltage-to-current converter for low I<sub>OUT</sub>
- Isolating current source
- · Differential output difference amplifier
- Isolating current source with buffering amplifier for greater accuracy
- Window comparator with window span and window center inputs
- Precision voltage-controlled current source with buffered differential inputs and gain
- Digitally controlled gain of ±1 amplifier



## 7 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

#### 7.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on Notifications to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 7.2 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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#### 7.3 Trademarks

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## 7.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 7.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

#### 8 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision * (November 1996) to Revision A (February 2024)	Page
•	Updated the numbering format for tables, figures, and cross-references throughout the document	1
	Implementation, Typical Applications, Device and Documentation Support, and Mechanical, Packaging, Orderable Information sections	and 1
•	Deleted DIP package and associated content from data sheet	1
•	Updated Features bullets	1
•	Updated Applications bullets	1
•	Added Pin Functions table	
•	Added dual supply specification to Absolute Maximum Ratings	3
•	Changed output short-circuit from "ground" to "V <sub>S</sub> / 2" in Absolute Maximum Ratings	3
•	Added $V_{REF} = 0V$ , $V_{CM} = V_S / 2$ , and $G = 1$ to test conditions in <i>Electrical Characteristics</i> and <i>Typical Characteristics</i> for clarity	4
•	Changed "Offset Voltage vs Temperature" to "Offset voltage drift" and added T <sub>A</sub> = –40°C to +85°C test condition for clarity	4
•	Changed "Offset Voltage vs Time" to "Long-term stability" for clarity	4
•	Changed "Offset Voltage vs Power Supply" to Power-supply rejection ratio for clarity	
•	Changed voltage noise typical value at 1kHz from 65nV/\(\sqrt{Hz}\) to 75nV/\(\sqrt{Hz}\)	
•	Changed "Gain Error vs Temperature" to "Gain error drift" and added T <sub>A</sub> = –40°C to +85°C test condition for clarity	

Product Folder Links: INA132

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•	Changed "Voltage, Positive" to "Positive output voltage swing" and from "Voltage, Negative" to "Negative output voltage swing"	.4
•	Added test condition of "Continuous to V <sub>S</sub> / 2" to short-circuit current for clarity	4
•	Changed short-circuit current typical value from ±12mA to +6mA/–15mA	.4
•	Deleted power supply voltage range typical value of ±15V	. 4
•	Moved voltage range, operating temperature range, and thermal resistance from <i>Electrical Characteristics</i> to <i>Recommended Operating Conditions</i> and <i>Thermal Information</i>	) . <mark>4</mark>
•	Changed quiescent current typical value from ±160μA to ±175μA and maximum value from ±185μA to ±230μA	4
•	Added $V_{REF} = V_S / 2$ , $V_{CM} = V_S / 2$ , and $G = 1$ to test conditions in <i>Electrical Characteristics:</i> $V_S = 5V$ for clarity	5
•	Changed "Offset Voltage vs Temperature" to "Offset voltage drift" and added T <sub>A</sub> = -40°C to +85°C test condition for clarity	.5
•	Added (V–) to negative output voltage swing minimum and typical values	.5
•	Deleted power supply voltage range typical value of +5V	.5
•	Moved voltage range from Electrical Characteristics: $V_S = 5V$ to Recommended Operating Conditions	5
•	Changed quiescent current typical value from ±155μA to ±175μA and maximum value from ±185μA to	
	±230µA	. 5

# 9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 18-Sep-2024

#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
INA132U	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI		INA 132U	
INA132U/2K5	ACTIVE	SOIC	D	8	2500	RoHS & Green	Call TI   NIPDAU	Level-3-260C-168 HR		INA 132U	Samples
INA132UA	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI	-40 to 85	INA 132U A	
INA132UA/2K5	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 85	INA 132U A	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



# PACKAGE OPTION ADDENDUM

www.ti.com 18-Sep-2024

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# **PACKAGE MATERIALS INFORMATION**

www.ti.com 30-Nov-2023

## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA132U/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
INA132UA/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 30-Nov-2023



#### \*All dimensions are nominal

Device	Device Package Type		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
INA132U/2K5	SOIC	D	8	2500	356.0	356.0	35.0	
INA132UA/2K5	SOIC	D	8	2500	356.0	356.0	35.0	

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www.ti.com 30-Nov-2023

## **TUBE**



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)	
INA132U	D	SOIC	8	75	506.6	8	3940	4.32	
INA132UA	D	SOIC	8	75	506.6	8	3940	4.32	



SMALL OUTLINE INTEGRATED CIRCUIT



## NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



#### NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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